

CLAIMS

1. A method for controlling an SCR-type switch, consisting of applying on the switch gate several periods of an unrectified high-frequency voltage, the power of one HF halfwave being insufficient to start the SCR-type switch.
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2. The control method of claim 1, wherein the HF voltage oscillates at a selected frequency between 10 kHz and a few GHz.
3. The method of claim 1, wherein the high frequency is applied via an
10 insulating layer formed above a sensitive area of the component.
4. The method of claim 3, wherein the high frequency is applied above a gate region of a thyristor.
- 15 5. The method of claim 3, wherein the high frequency is applied above a gate region of a triac.
6. The method of claim 3, wherein the high frequency is applied via a high-frequency line.
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7. The method of claim 3, wherein the high frequency is applied via a winding.
8. An SCR-type switch component, comprising two main electrodes and at
25 least one control electrode formed on an insulating layer (45) and arranged above a starting region of the component, said control electrode being intended to be connected to an unrectified HF power supply.
9. The method of claim 8, wherein the control electrode is arranged above a
30 gate region (42) of a thyristor.
10. The method of claim 8, wherein the control electrode is arranged above a

gate region (52) of a triac.

11. The method of claim 8, wherein the control electrode is a high-frequency line (61).

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12. The method of claim 8, wherein the high frequency is applied via a winding (71).